

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Tae-Hee CHOE, et al.

Serial No.

[Division of Serial No. 09/989,112, filed November 21, 2001]

Filed: November 17, 2003

For: SOI SUBSTRATE HAVING AN ETCH STOP LAYER, AND FABRICATION METHOD
THEREOF, SOI INTEGRATED CIRCUIT FABRICATED THEREON, AND
METHOD OF FABRICATING SOI INTEGRATED CIRCUIT USING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents

Alexandria, VA 22313-1450

Sir:

Prior to calculation of the statutory filing fee, kindly amend the application identified above as follows:

IN THE CLAIMS

Cancel Claims 26-41 without prejudice or disclaimer.

Amendments to the claims are reflected in the listing of claims which begins on page 2 of this Amendment.